## In the Claims

Claims 1-46 (canceled)

- 47. (previously presented) A dual gate oxide complementary metal oxide semiconductor (CMOS) RF power amplifier for a wireless transmission system comprising:
- RF power amplifier input stage circuitry including devices with a first gate oxide thickness;
- RF power amplifier output stage circuitry having devices with a second gate oxide thickness; and

wherein the first gate oxide thickness is less than the second gate oxide thickness.

- 48. (previously presented) The RF power amplifier of claim 47, wherein the first gate oxide thickness is approximately 70 Angstroms.
- 49. (previously presented) The RF power amplifier of claim 47, wherein the second gate oxide thickness is approximately 140 Angstroms.
- 50. (previously presented) The RF power amplifier of claim 47, wherein the input stage further comprises one or more inverters.
- 51. (previously presented) The RF power amplifier of claim 50, wherein the output stage further comprises a plurality of switching devices.

- 52. (previously presented) A cellular telephone apparatus comprising:

  a transceiver for transmitting and receiving signals;

  a complementary metal oxide semiconductor (CMOS) RF power amplifier coupled to

  the transceiver, the RF power amplifier having input stage circuitry including

  devices with a first gate oxide thickness and output stage circuitry having

  devices with a second gate oxide thickness, wherein the first gate oxide

  thickness is less than the second gate oxide thickness; and

  an antenna coupled to the RF power amplifier and the transceiver for transmitting and

  receiving signals.
- 53. (previously presented) The cellular telephone apparatus of claim 52, wherein the first gate oxide thickness is approximately 70 Angstroms.
- 54. (previously presented) The cellular telephone apparatus of claim 52, wherein the second gate oxide thickness is approximately 140 Angstroms.
- 55. (previously presented) The cellular telephone apparatus of claim 52, wherein the input stage further comprises one or more inverters.
- 56. (previously presented) The cellular telephone apparatus of claim 55, wherein the output stage further comprises a plurality of switching devices.

10/813,589 3 of 8 Attorney Docket No.: SIL.P0078

- 57. (currently amended) A method of providing a CMOS RF power amplifier for a wireless transmission system comprising the steps of:
- providing an input stage including one or more devices having a first gate oxide thickness;
- providing an output stage including a plurality of switching devices having a second gate oxide thickness; and
- selecting the thickness of the first and second gate oxides such that the second gate oxide thickness is greater than the first gate oxide thickness.
- 58. (currently amended) The method of claim 57, further comprising the step of forming the RF power amplifier on a single integrated circuit.
- 59. (previously presented) The method of claim 57, wherein the first gate oxide thickness is approximately 70 Angstroms.
- 60. (previously presented) The method of claim 57, wherein the second gate oxide thickness is approximately 140 Angstroms.
- 61. (previously presented) The method of claim 57, wherein the first portion forms a preamplifier circuit.
- 62. (previously presented) The method of claim 61, wherein the second portion forms an amplifier circuit.